MBN1500E33E2

Silicon N-channel IGBT 3300V E2 version

FEATURES

∗ Soft switching behavior & low conduction loss:
Soft low-injection punch-through High conductivity IGBT.
∗ Low driving power due to low input capacitance MOS gate.
∗ Low noise recovery: Ultra soft fast recovery diode.
∗ High thermal fatigue durability:
(delta Tc=70K, N>30,000cycles)
AlSiC base-plate/AlN substrate

ABSOLUTE MAXIMUM RATINGS (Tc=25ºC)

Item		Symbol	Unit	MBN1500E33E2
Collector Emitter Voltage		V_{CES}	V	3,300
Gate Emitter Voltage		V_{GES}	V	±20
Collector Current	DC	I_C	A	1,500 (Tc=95 ºC)
	1ms	I_{Cp}		3,000
Forward Current	DC	I_F	A	1,500
	1ms	I_{FM}		3,000
Junction Temperature		T_j	ºC	-40 ~ +150
Storage Temperature		T_{stg}	ºC	-50 ~ +125
Isolation Voltage		V_{ISO}	V_{RMS}	6,000(AC 1 minute)
Screw Torque	Terminals (M4/M8)	-	N·m	2/15 (1)
	Mounting (M6)	-		6 (2)

Notes: (1) Recommended Value $1.8\pm0.2/15^{+0}_{-3}$N·m (2) Recommended Value 5.5±0.5N·m

ELECTRICAL CHARACTERISTICS

Item		Symbol	Unit	Min.	Typ.	Max.	Test Conditions
Collector Emitter Cut-Off Current		I_{CES}	mA	-	-	12	V_{CE}=3,300V, V_{GE}=0V, Tj=25ºC
				-	20	60	V_{CE}=3,300V, V_{GE}=0V, Tj=125ºC
Gate Emitter Leakage Current		I_{GES}	nA	-500	-	+500	V_{GE}=±20V, V_{CE}=0V, Tj=25ºC
Collector Emitter Saturation Voltage		$V_{CE(sat)}$	V	2.5	2.95	3.5	I_C=1,500A, V_{GE}=15V, Tj=125ºC
				-	3.1	-	I_C=1,500A, V_{GE}=15V, Tj=150ºC
Gate Emitter Threshold Voltage		$V_{GE(TO)}$	V	5.5	6.3	7.5	V_{CE}=10V, I_C=1,500mA, Tj=25ºC
Input Capacitance		C_{ies}	nF	-	195	-	V_{CE}=10V, V_{GE}=0V, f=100kHz, Tj=25ºC
Internal Gate Resistance		Rge	Ω	-	1.0	-	V_{CE}=10V, V_{GE}=0V, f=100kHz, Tj=25ºC
Switching Times	Rise Time	t_r	µs	1.6	2.0	2.6	V_{CC}=1,650V, Ic=1,500A
	Turn On Time	t_{on}		2.0	3.0	3.7	Ls=100nH
	Fall Time	t_f		0.9	1.7	2.6	R_G=2.7Ω/2.7Ω, CGE=330nF (3)
	Turn Off Time	t_{off}		2.7	4.4	5.5	V_{GE}=±15V, Tj=125ºC
Peak Forward Voltage Drop		V_{FM}	V	2.2	2.6	3.0	IF=1,500A, V_{GE}=0V, Tj=125ºC
				-	2.6	-	IF=1,500A, V_{GE}=0V, Tj=150ºC
Reverse Recovery Time		t_{rr}	µs	0.2	0.8	1.2	Vcc=1,650V, IF=1,500A, Ls=100nH Tj=125ºC
Short Circuit Pulse Width		t_{sc}	µs	10	-	-	V_{CC}=2000V,Ls=80nH R_G(on/off)=2.7/27Ω, V_{GE}=±15V,Tj=125ºC
Turn On Loss		$E_{on(10\%)}$	J/P	-	2.9	3.6	Tj=125ºC
		$E_{on(full)}$		-	3.2	-	
				-	3.5	-	Tj=150ºC
Turn Off Loss		$E_{off(10\%)}$	J/P	-	2.2	2.6	Tj=125ºC
		$E_{off(full)}$		-	2.4	-	
				-	2.5	-	Tj=150ºC
Reverse Recovery Loss		$E_{rr(10\%)}$	J/P	-	1.4	1.9	Tj=125ºC
		$E_{rr(full)}$		-	1.7	-	
				-	2.1	-	Tj=150ºC

V_{CC}=1,650V, Ic=1,500A, Ls=100nH, R_G=2.7Ω/2.7Ω, CGE=330nF (3) V_{GE}=±15V

Notes:(3) R_G and C_{GE} value are the test condition's value for evaluation of the switching times, not recommended value. Please, determine the suitable R_G value after the measurement of switching waveforms (overshoot voltage, etc.) with appliance mounted.

* Please contact our representatives at order.
* For improvement, specifications are subject to change without notice.
* For actual application, please confirm this spec sheet is the newest revision.

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THERMAL CHARACTERISTICS

Item		Symbol	Unit	Min.	Typ.	Max.	Conditions
Thermal Impedance	IGBT	Rth(j-c)	K/W	-	-	0.0078	Junction to case
	FWD	Rth(j-c)		-	-	0.0156	
Contact Thermal Impedance		Rth(c-f)	K/W	-	0.005	-	Case to fin (λgrease=1W/(m･K), heat-sink flatness ≤50um)

MODULE MECHANICAL CHARACTERISTICS

Item		Unit	Characteristics	Conditions
Weight		g	1,300	
Stray inductance in module	LS(CM-EM)	nH	12	Collector-main to Emitter-main
	LS(ES-EM)		49	Emitter-sense to Emitter-main
	LS(CM-CS)		56	Collector-main to Collector sense
Terminal Resistance	$R_{Terminal}$	mΩ	0.09	Collector-main to Emitter-main
Comparative Tracking Index (CTI)			600	
Module base plate Material			Al-SiC	
Baseplate Thickness		mm	5	
Insulation plate Material			Al N	
Terminal Surface treatment			Ni plating	
Case Material			Poly-Phenilene Sulfide	
Fire and Smoke Category			I2 / F3	NFF 16-102

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DEFINITION OF TEST CIRCUIT

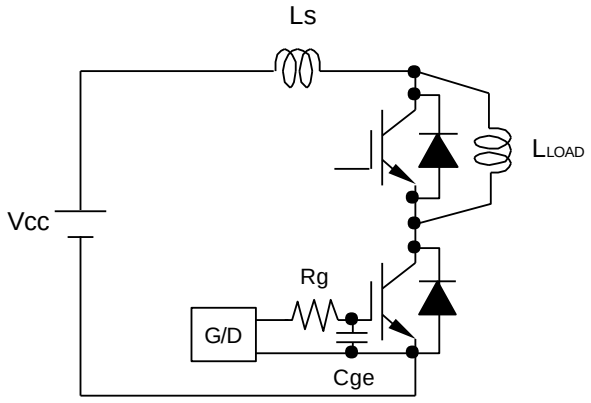


Fig.1 Switching test circuit

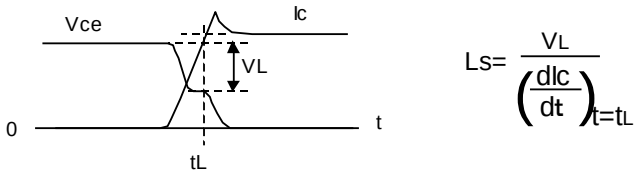
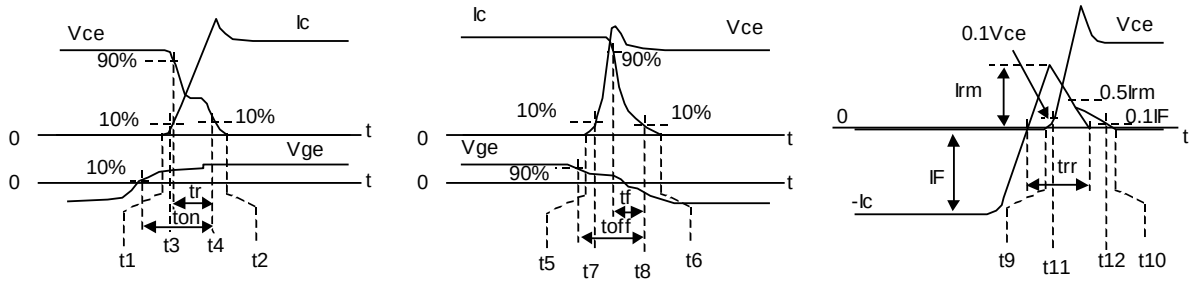


Fig.2 Definition of stray inductance



$$Eon(10\%)=\int_{t3}^{t4} Ic\cdot Vce\,dt \qquad Eoff(10\%)=\int_{t7}^{t8} Ic\cdot Vce\,dt \qquad Err(10\%)=\int_{t11}^{t12} IF\cdot Vce\,dt$$

$$Eon(Full)=\int_{t1}^{t2} Ic\cdot Vce\,dt \qquad Eoff(Full)=\int_{t5}^{t6} Ic\cdot Vce\,dt \qquad Err(Full)=\int_{t9}^{t10} IF\cdot Vce\,dt$$

Fig.3 Definition of switching loss

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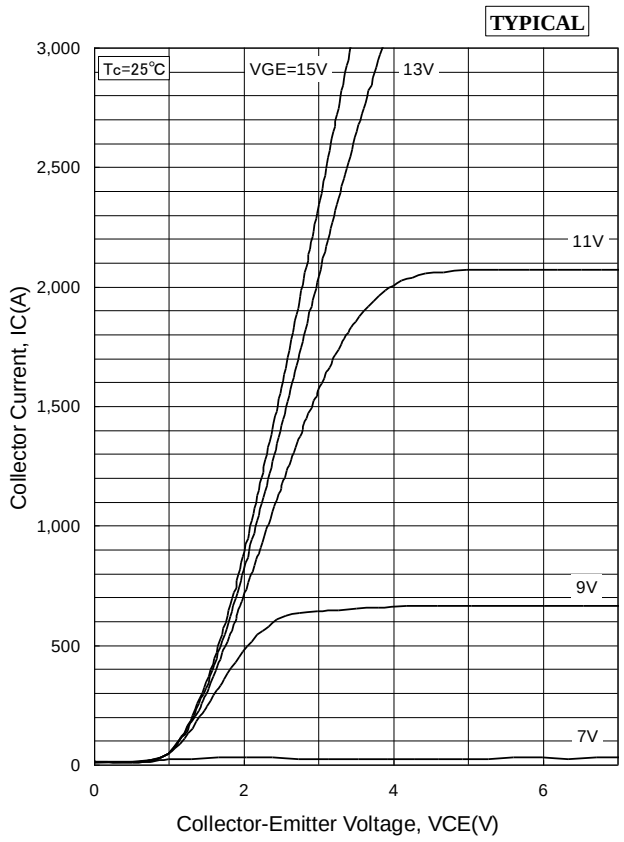
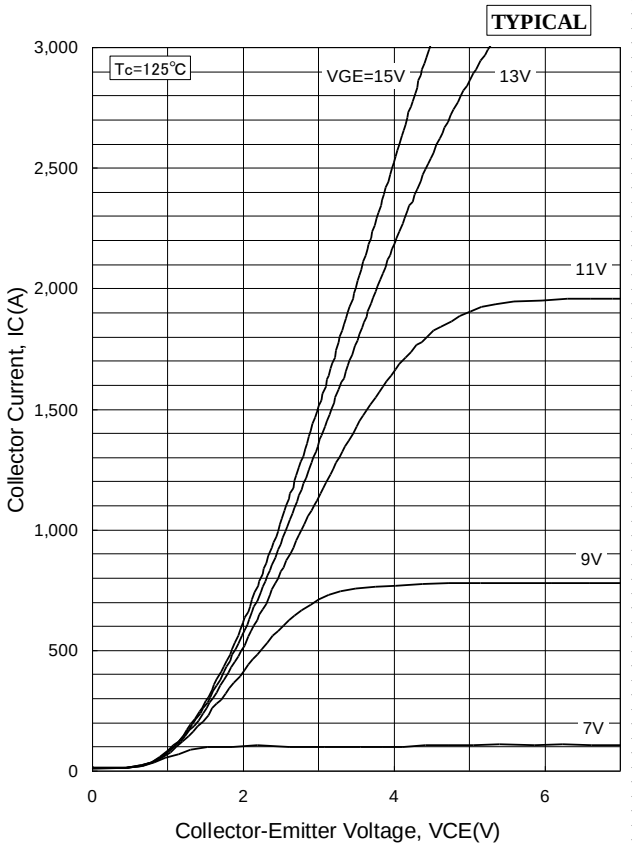
CHARACTERISTICS CURVE

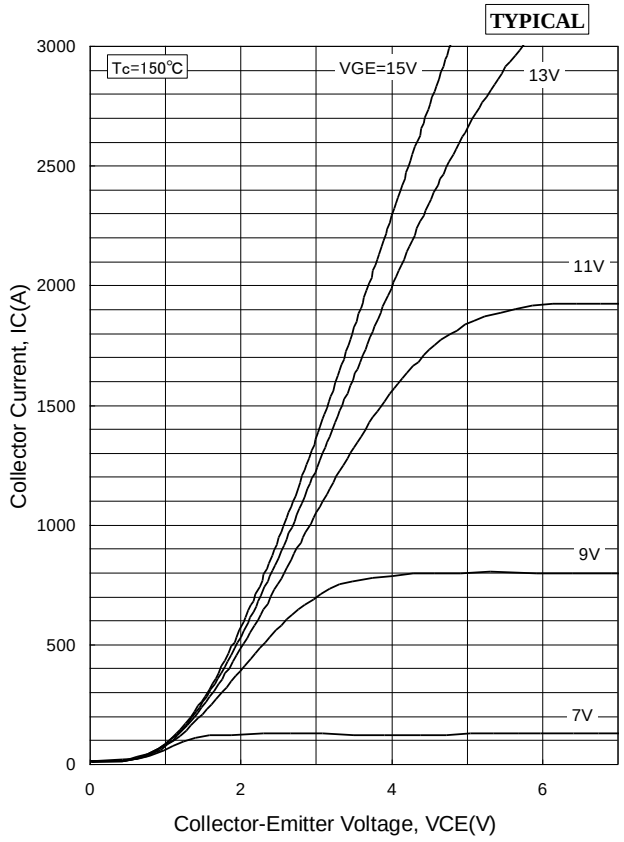
STATIC CHARACTERISTICS



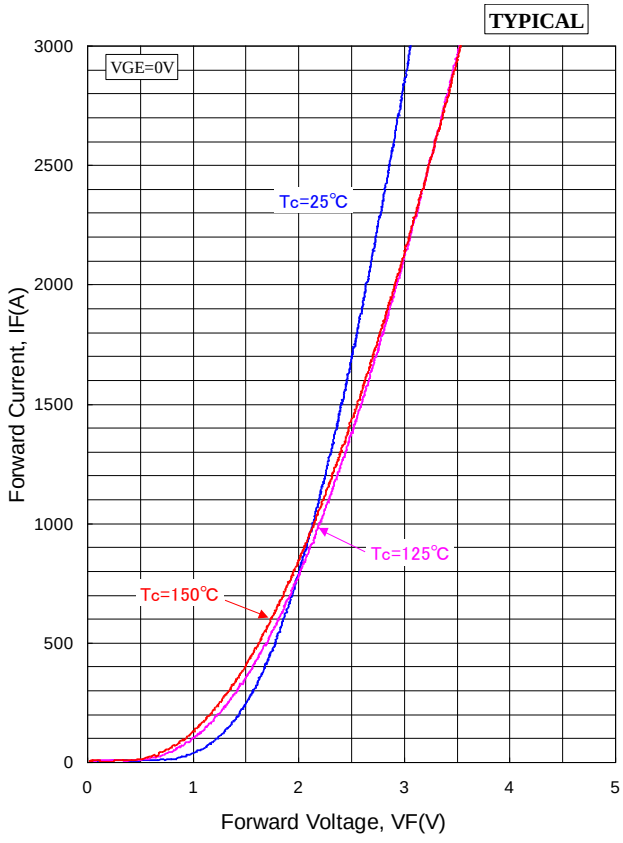
Collecter Current vs. Collector to Emitter Voltage



Collecter Current vs. Collector to Emitter Voltage



Collecter Current vs. Collector to Emitter Voltage



Forward Voltage of free-wheeling diode

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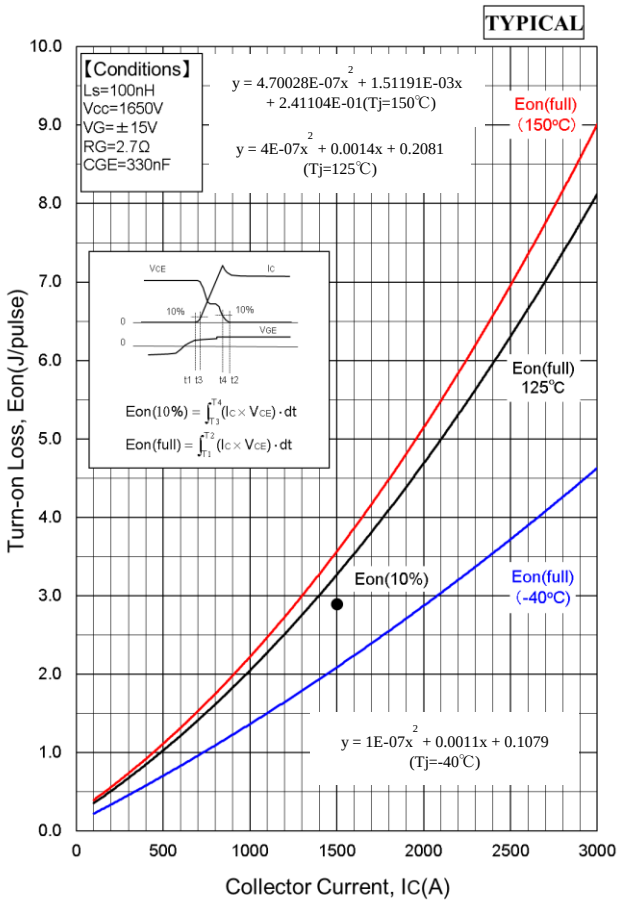
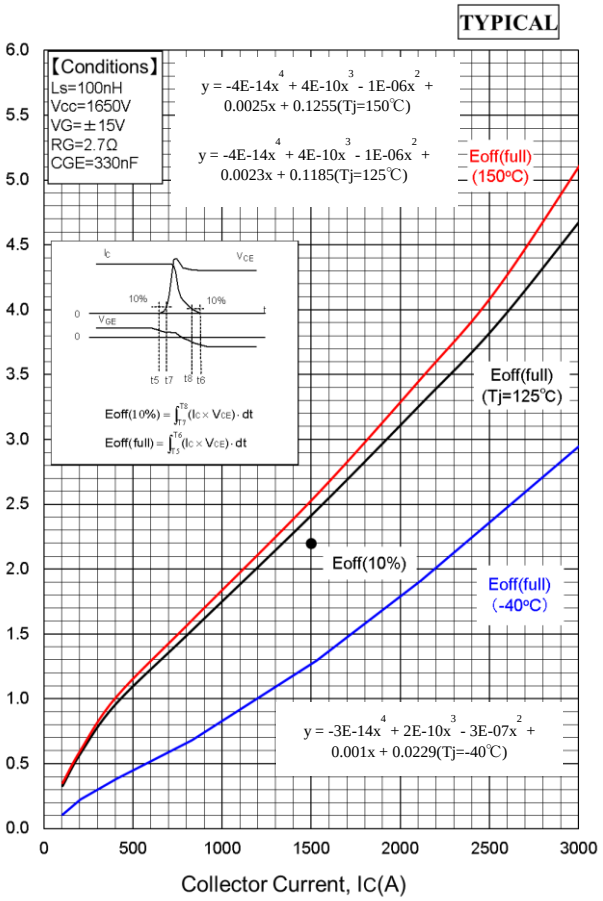
DYNAMIC CHARACTERISTICS

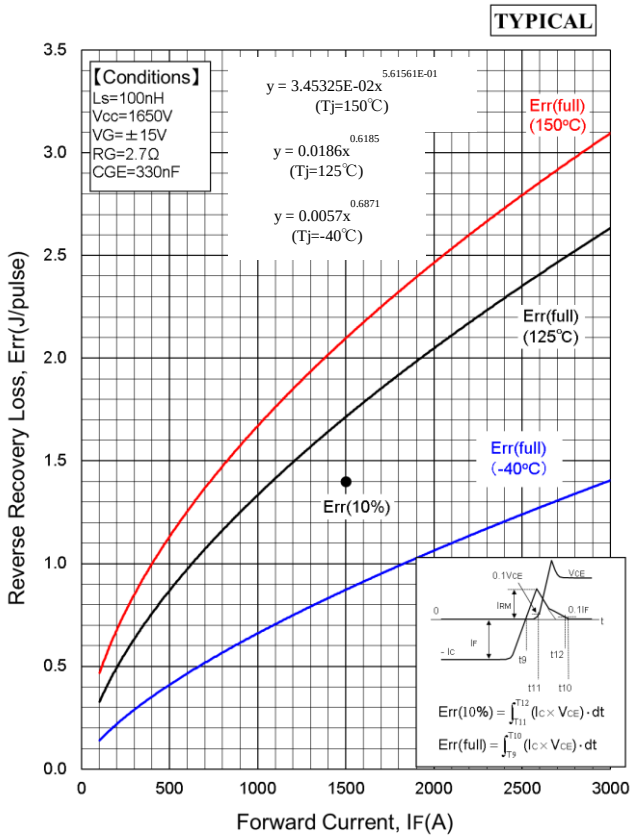
DEPENDENCE OF CURRENT



Turn-on Loss vs. Collector Current



Turn-off Loss vs. Collector Current



Recovery Loss vs. Forward Current

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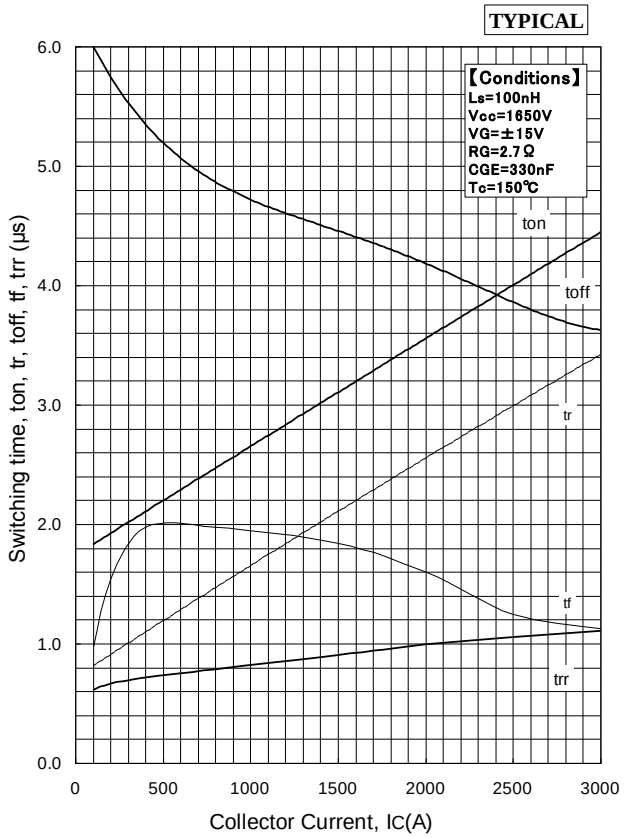
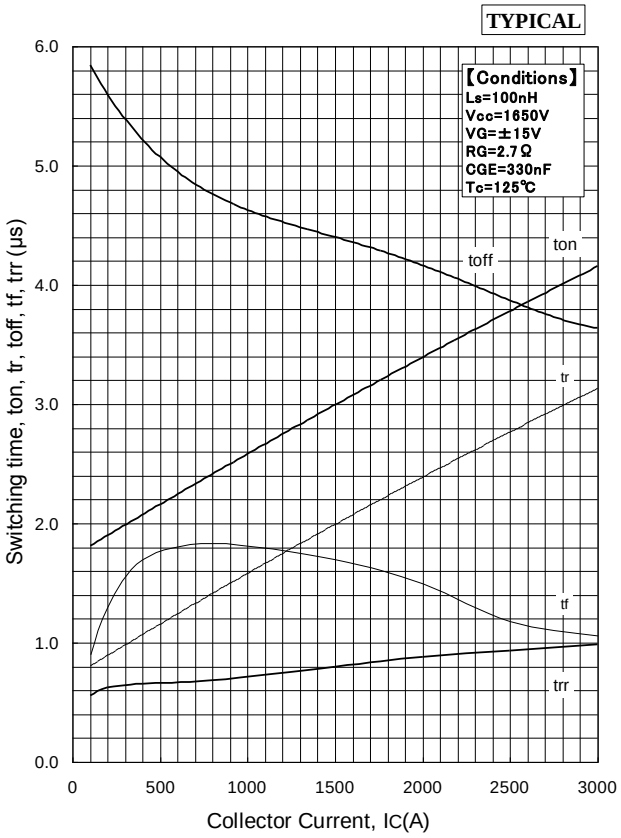
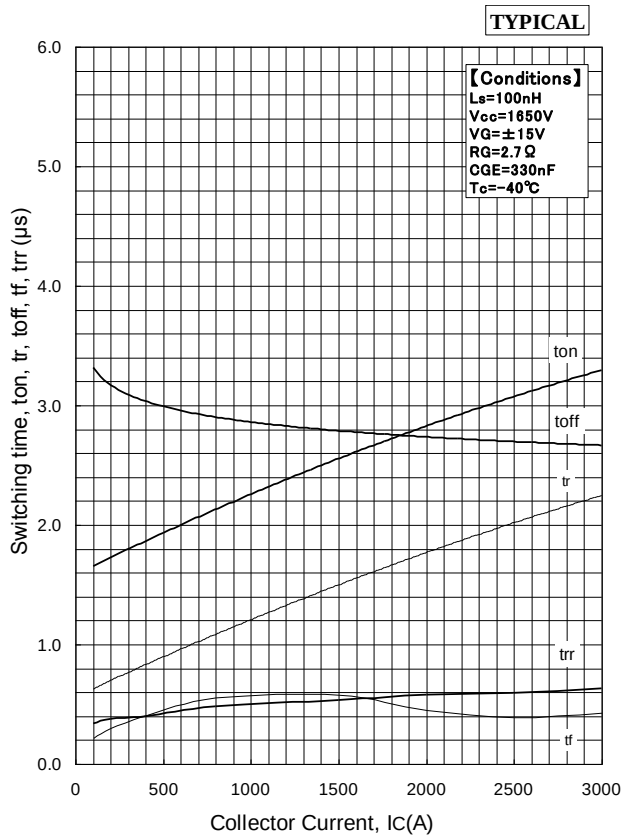


Switching time vs. Collector current



Switching time vs. Collector current



Switching time vs. Collector current

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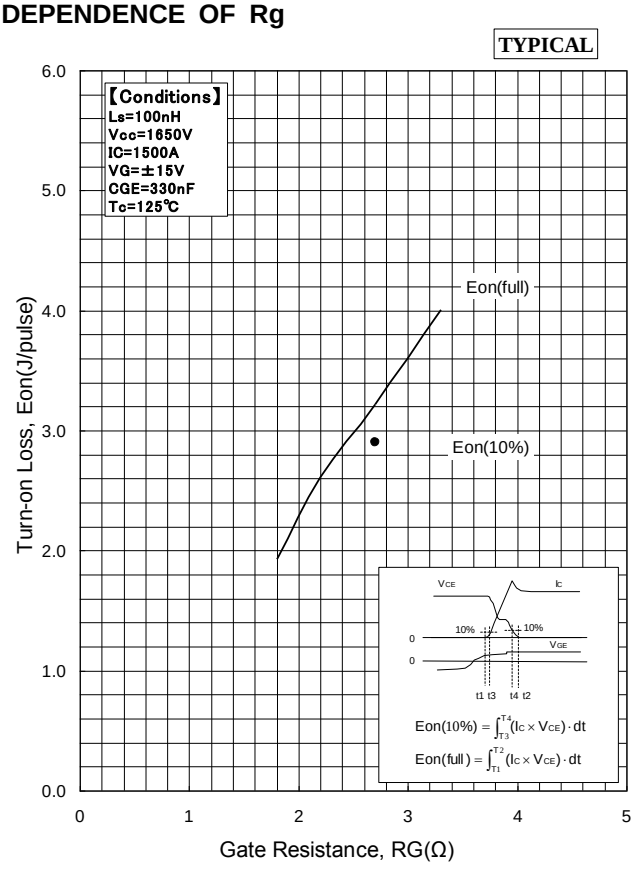
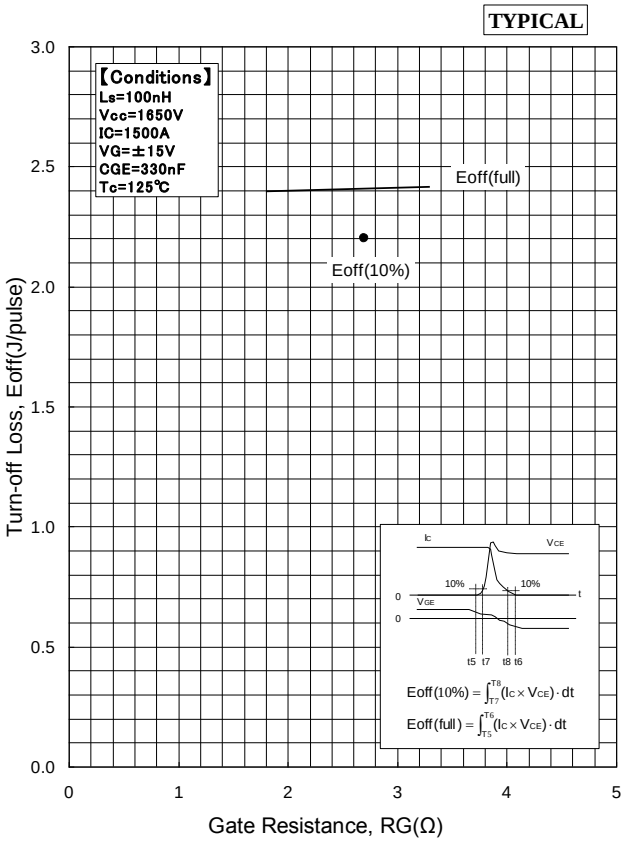
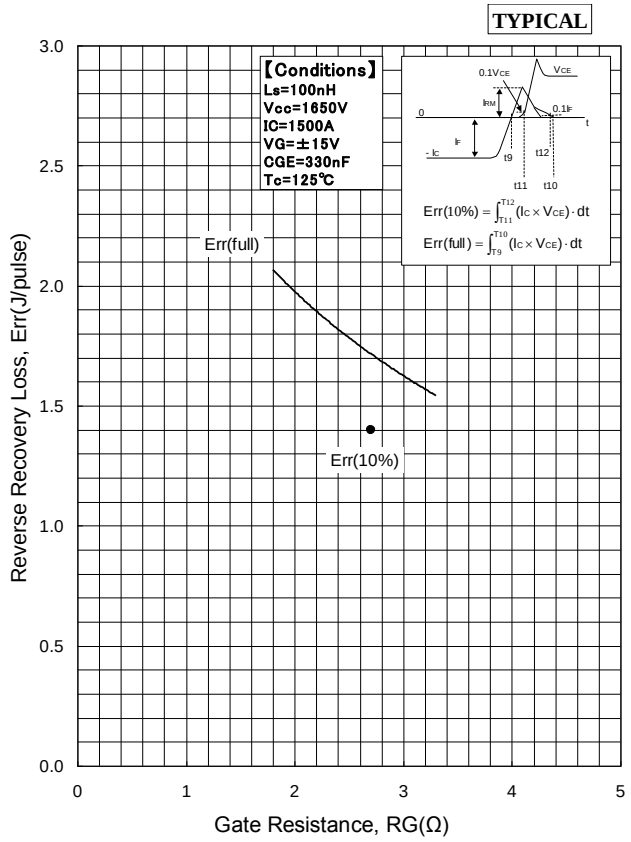
DEPENDENCE OF Rg



Turn-on Loss vs. Gate Resistance



Turn-off Loss vs. Gate Resistance



Recovery Loss vs. Gate Resistance

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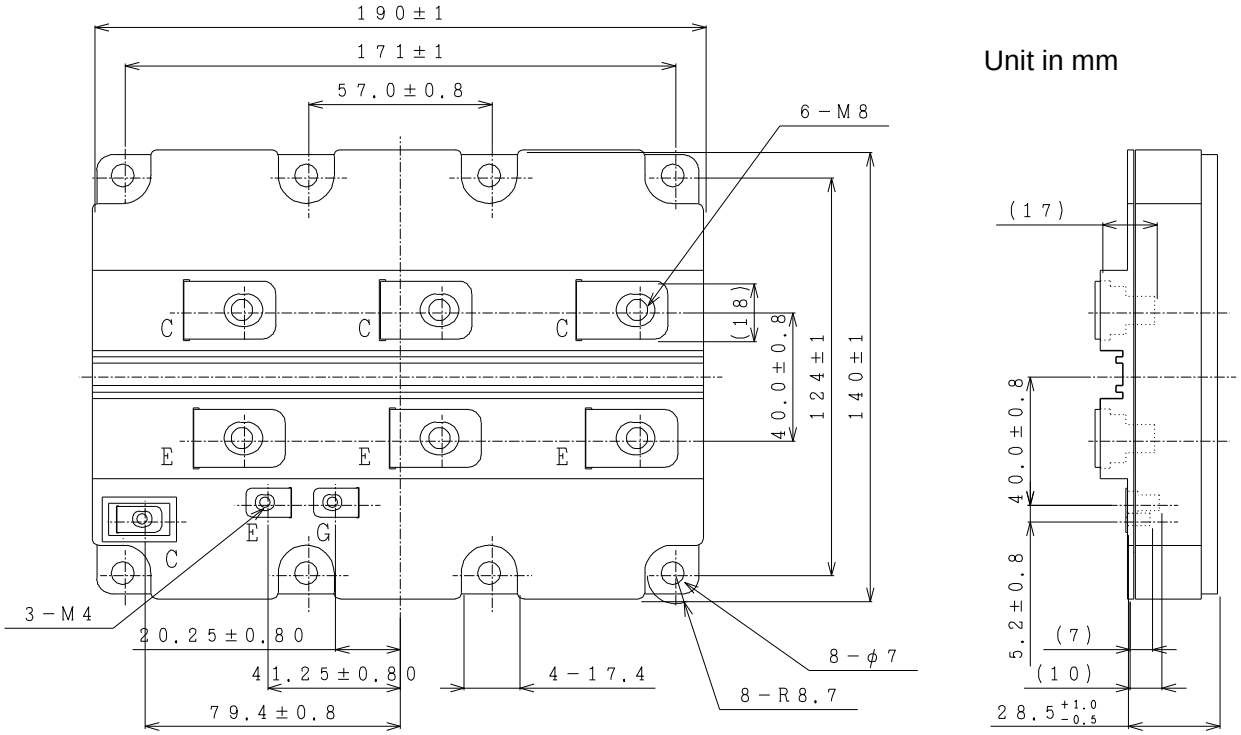
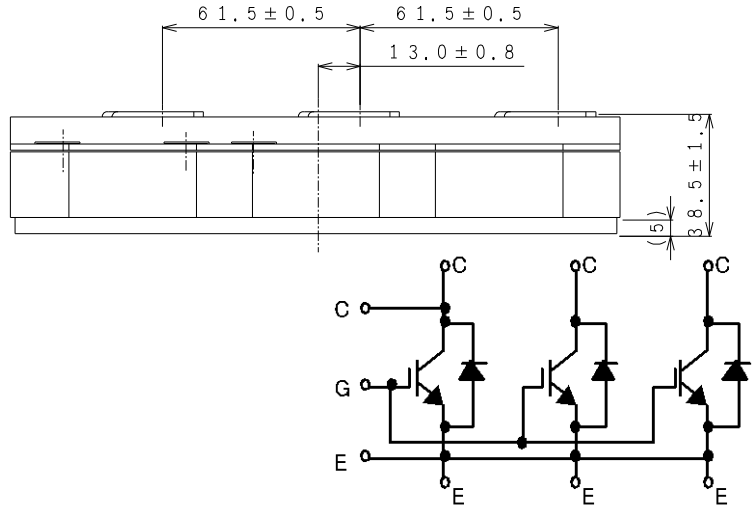
OUTLINE DRAWINGS

Unit in mm





Circuit diagram

Material declaration

Please note the following materials are contained in the product, in order to keep characteristic and reliability level.

Material	Contained part
Lead (Pb) and its compounds	Solder

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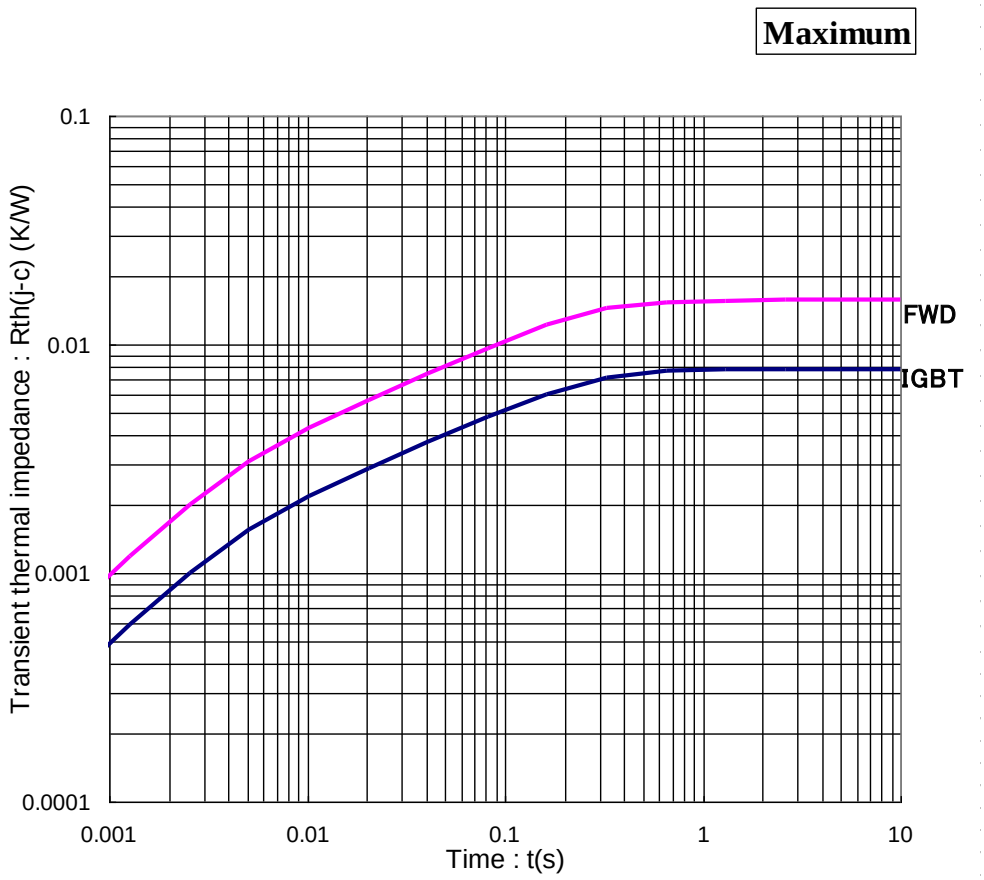
TRANSIENT THERMAL IMPEDANCE



Transient Thermal Impedance Curve

Curve approximation model
Zth = Σ rth[n]*(1-exp(-t/τth[n]))

n	1	2	3	4	Unit
τ th[n]	1.60E-01	2.74E-02	4.04E-03	7.37E-04	sec
rth[n,IGBT]	4.83E-03	1.40E-03	1.40E-03	1.43E-04	K/W
rth[n,Diode]	9.62E-03	2.90E-03	2.74E-03	2.93E-04	K/W

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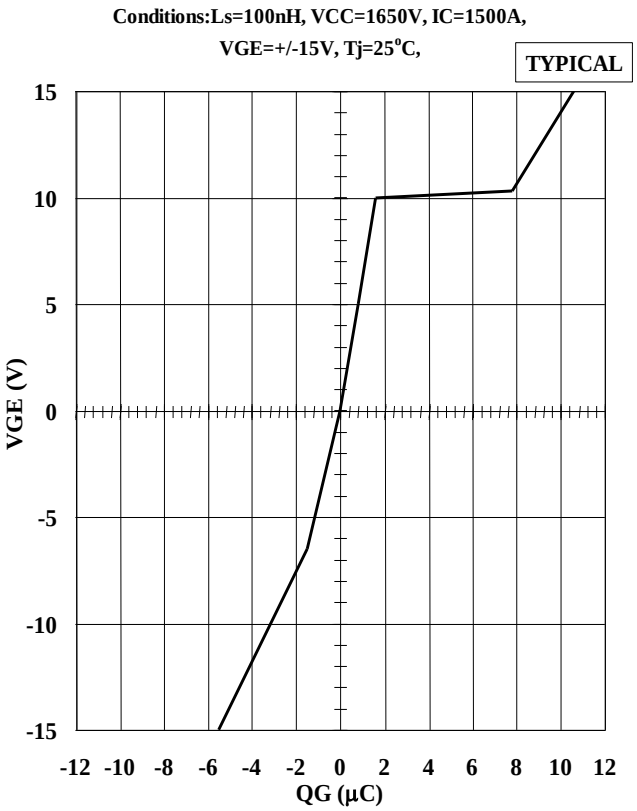
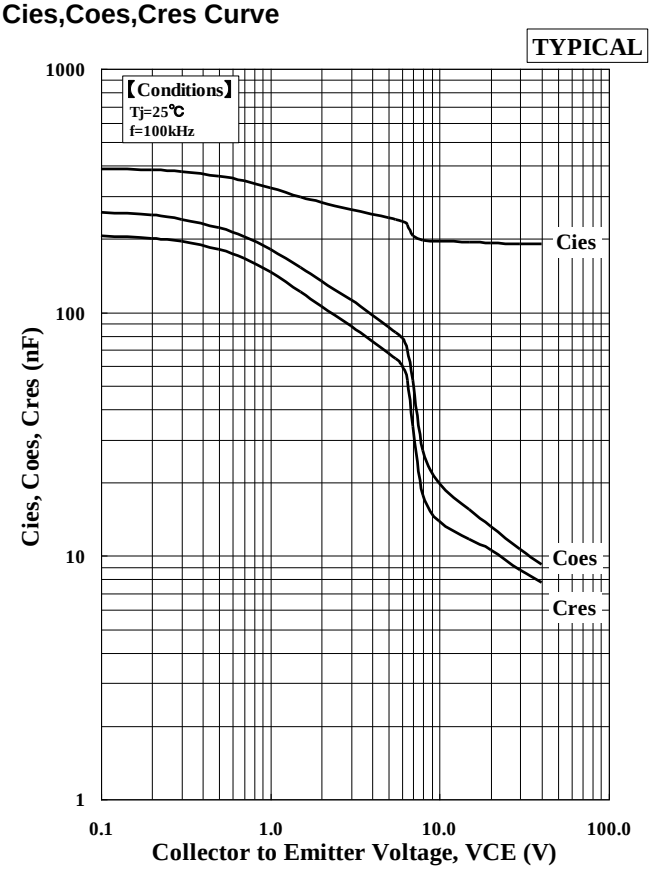
QG-VG CURVE



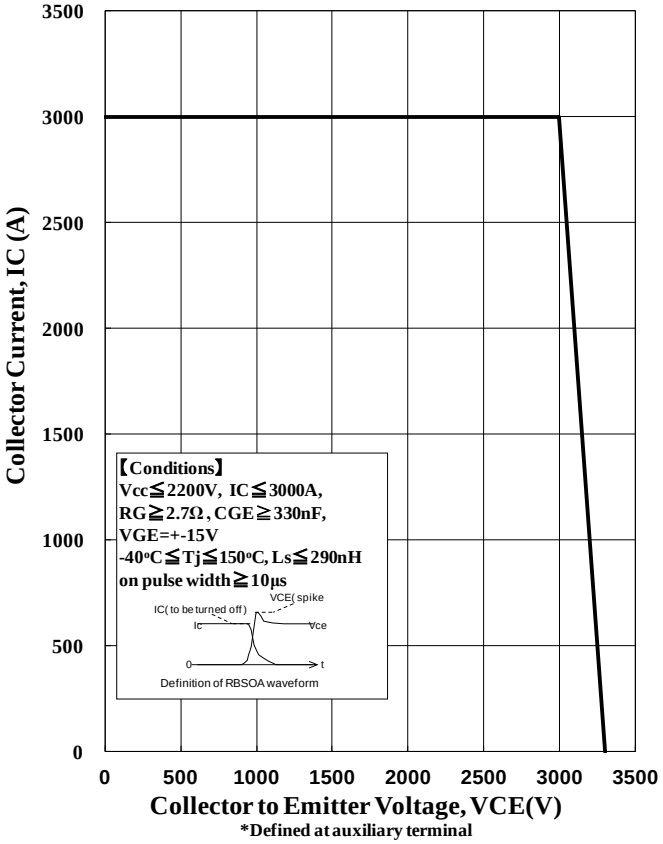
QG-VGE curve

Cies,Coes,Cres Curve

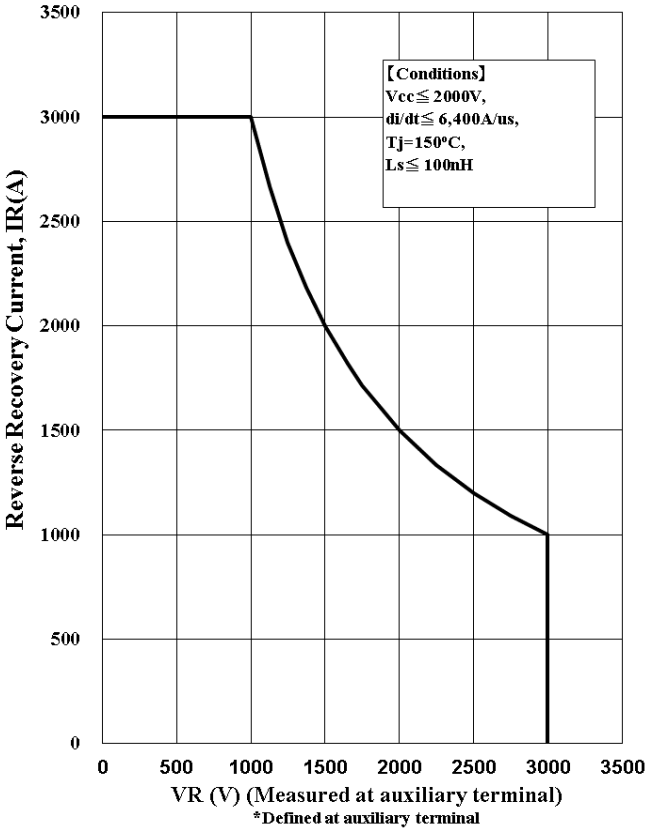


Capacitance vs. Collector to Emitter Voltage

Safe operation area



Reverse bias Safe operation area(RBSOA)



Reverse recovery Safe operation area(RecSOA)

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HITACHI POWER SEMICONDUCTORS

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